

SEMICONDUCTOR®

BC516

PNP Darlington Transistor

- This device is designed for applications reguiring extremely high current gain at currents to 1mA.
- Sourced from process 61.



1. Collector 2. Base 3. Emitter

Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	10	V	
I _C	Collector Current - Continuous	1	А	
PD	Total Power Dissipation $T_A = 25^{\circ}C$	625	mW	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C	

Electrical Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 2{\rm mA}, I_{\rm B} = 0$	30			V
V _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	40			V
V _{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu A, I_{\rm C} = 0$	10			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 30V, I_{E} = 0$			100	nA
h _{FE}	DC Current Gain	$I_{C} = 20$ mA, $V_{CE} = 2V$	30,00 0			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 100mA, I _B = 0.1mA			1	V
V _{BE} (on)	Base-Emitter On Voltage	I _C = 10mA, V _{CE} = 5V			1.4	V
f _T	Current Gain Bandwidth Product (2)	$I_{C} = 10$ mA, $V_{CE} = 5$ V, f = 100MHz		200		MHz

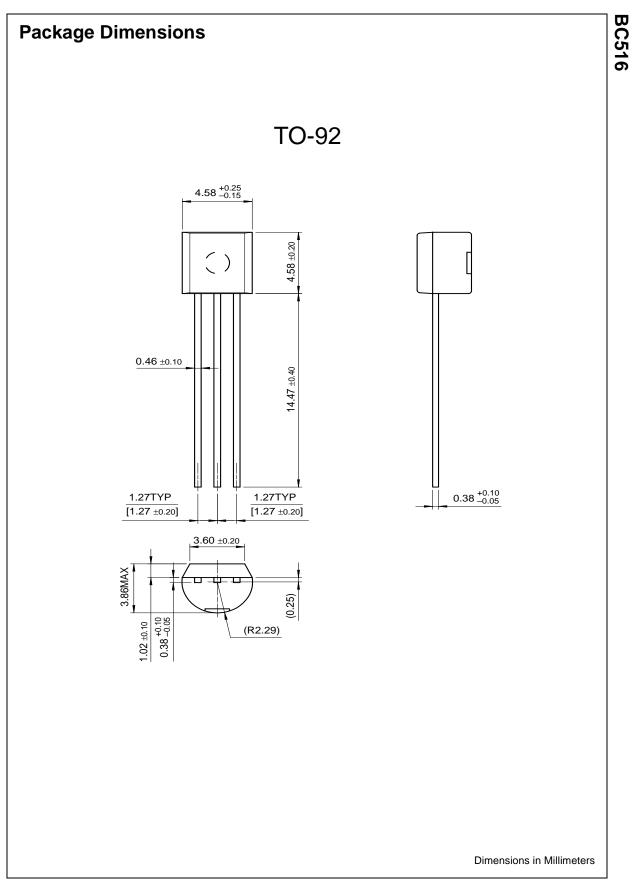
NOTES: 1. Pulse Test Pulse Width $\leq 2\%$

2. $f_T = Ih_{fe}I \cdot f_{test}$

Thermal Characteristics $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W

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